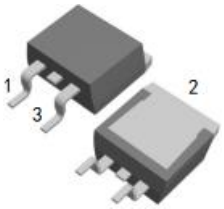
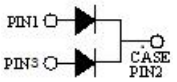
Plastic-Encapsulate Diodes Schottky Rectifier

Features

- ●FRED (Planar) wafer construction
- ●Ultrafast recovery time
- ● Low forward voltage drop, low power losses
- ● High efficiency operation
  Plastic package has underwriters Laboratory
- ● Flammability Classification 94V-0



T0-263



Mechanical Data

- ● Case: Epoxy, Molded
- ● Weight: 1.9grams（approximately）
- ● Lead Temperature for Soldering Purposes: 260°C Max. for 10 sec
- ● Shipped 50 units per plastic tube
- ● Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable

Maximum Ratings & Electrical Characteristics

(T_A=25℃ unless otherwise noted)

PARAMETER	TEST CONDITIONS		SYMBOL	AS15M1200T	UNIT
Maximum repetitive peak reverse voltage			V_{RRM}	1200	V
Working peak reverse voltage			V_{RWM}	1200	V
Maximum DC blocking voltage			V_{DC}	1200	V
Maximum average forward rectified current at T_c=105°C total device per diode			I_F(AV)	15	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode			I_{FSM}	200	A
Voltage rate of change（rated V_R）			Dv/dt	10000	V/us
Operating junction temperature range			T_J	-55 to+150	°C
Storage temperature range			T_{STG}	-55 to+150	°C
Maximum Reverse Recover Time （If=0.5Amp, IR=1.0Amp,Irec=0.25Amp）	Trr		Trr	50	ns
Maximum instantaneous forward voltage per leg	I_F=15A I_F=15A	T_C=25℃ T_C=125℃	V_F	2.50 2.00	V
Maximum reverse current per leg at working peak Reverse voltage		T_J=25℃ T_J=100°C	I_R	10 500	uA uA

Thermal Characteristics T_A=25℃ unless otherwise noted

Symbol	Parameter	TYP	Unit
RθJC	Thermal Resistance, Junction to Case per Leg	4.0	°C /W
RθJA	Thermal Resistance, Junction to Ambient per Leg	62.5	°C /W

Note：Pulse test:300us pulse width, duty cycle=2%

Plastic-Encapsulate Diodes Schottky Rectifier

Ratings and Characteristics Curves

(T_A = 25℃ unless otherwise noted)

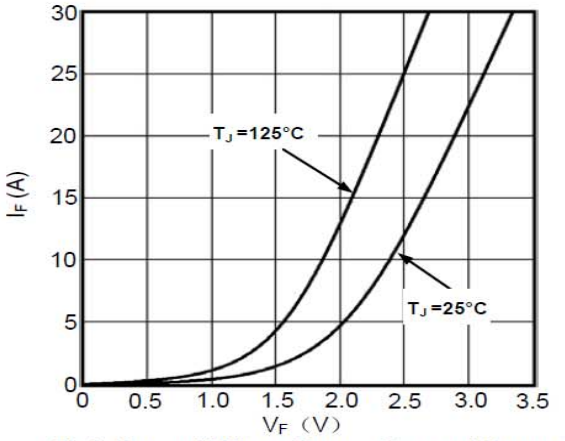


Fig1. Forward Voltage Drop vs Forward Current

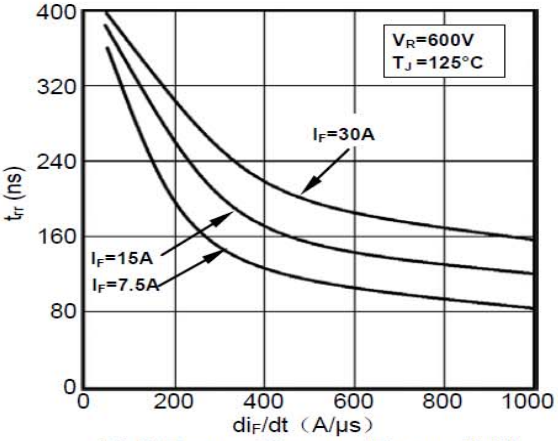


Fig2. Reverse Recovery Time vs di_F/dt

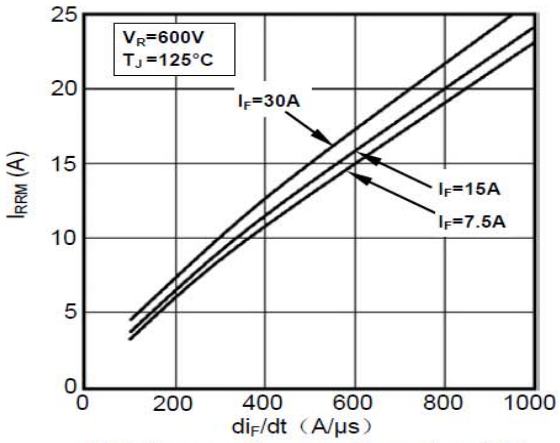


Fig3. Reverse Recovery Current vs di_F/dt

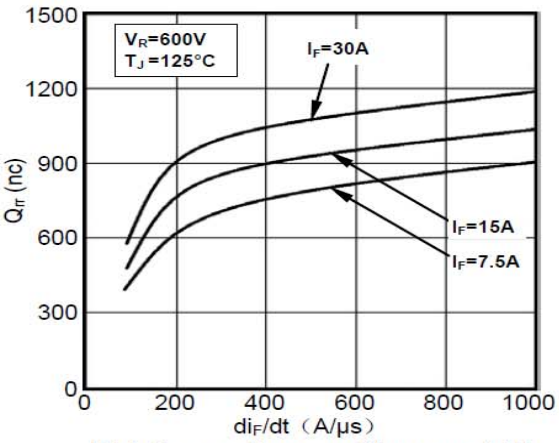


Fig4. Reverse Recovery Charge vs di_F/dt

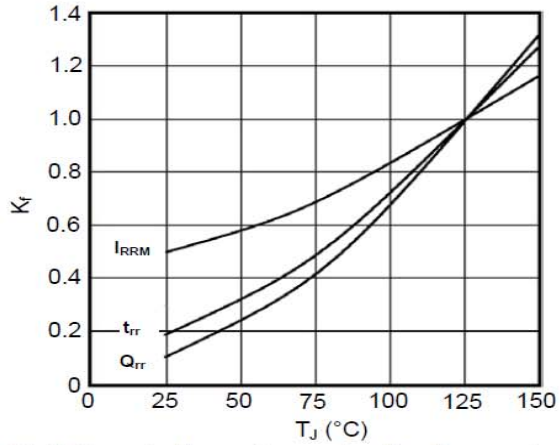


Fig5. Dynamic Parameters vs Junction Temperature

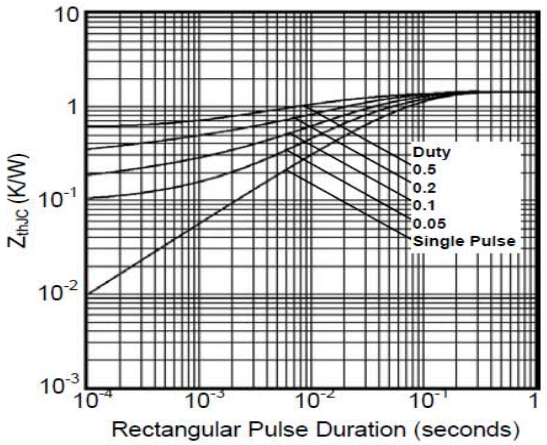
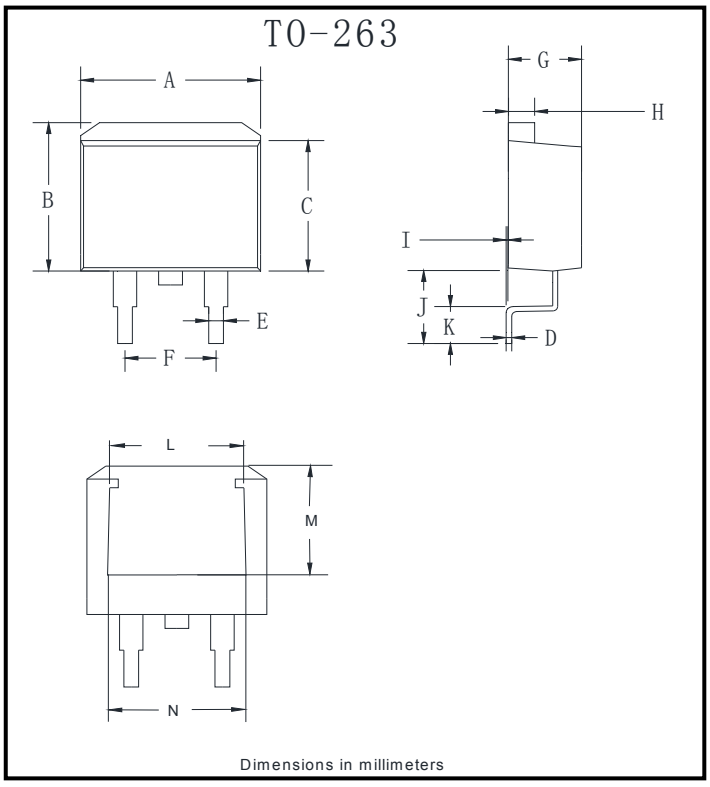


Fig6. Transient Thermal Impedance

Plastic-Encapsulate Diodes Schottky Rectifier

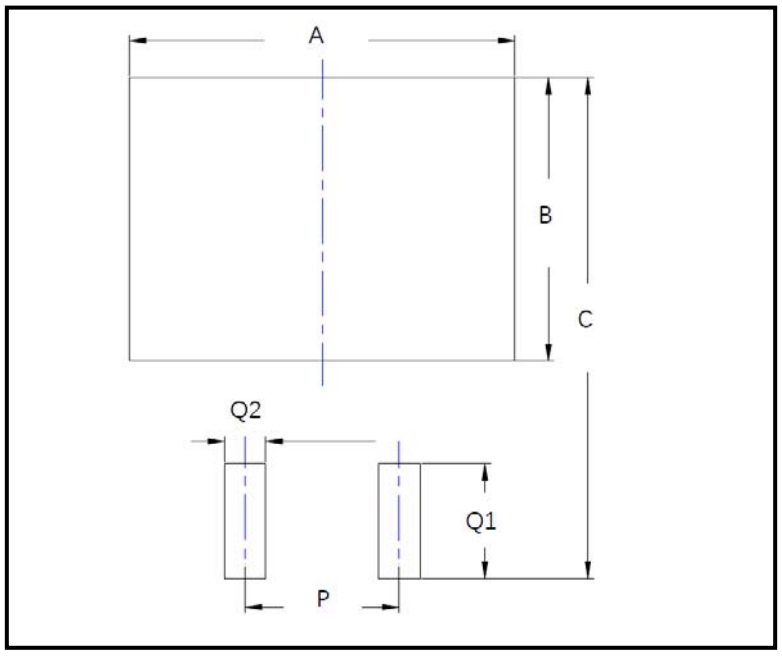
Package Outline Dimensions

■Outline Dimensions



TO-263		
Dim	Min	Max
A	9.5	11.5
B	9.7	10.5
C	8.4	9.0
D	0.28	0.64
E	0.68	0.94
F	4.55	5.6
G	4.04	5.10
H	1.14	1.4
I	0	0.2
J	4.9	6.05
K	1.79	2.79
L	7.3	7.9
M	6.2	6.8
N	7.6	8.2

■ Suggested Pad Layout



Dim	Millimeters
A	12.7
B	9.4
C	16.6
P	5.08
Q1	3.8
Q2	1.35